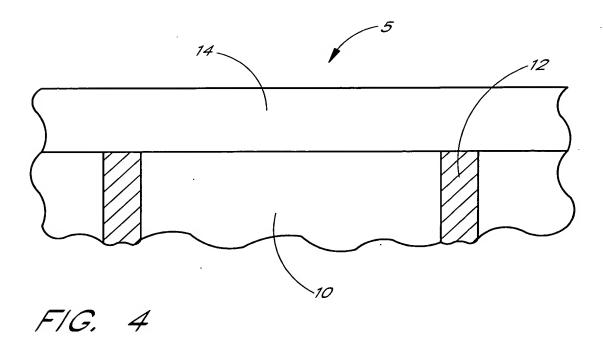
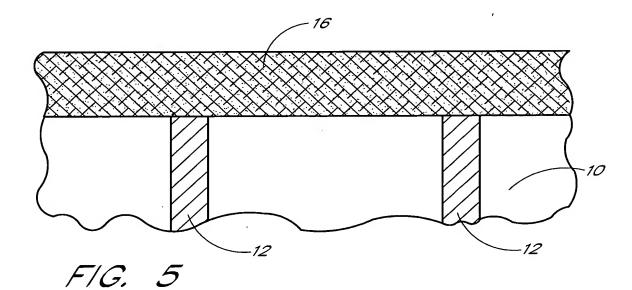
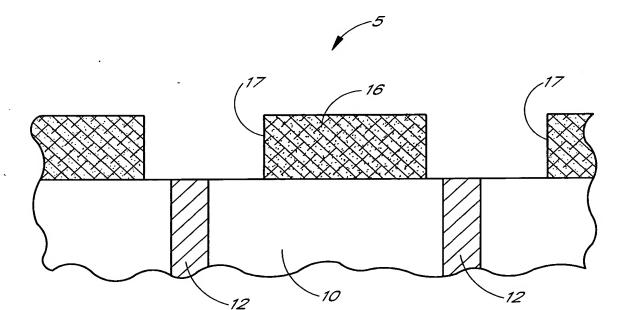


FIG. 3



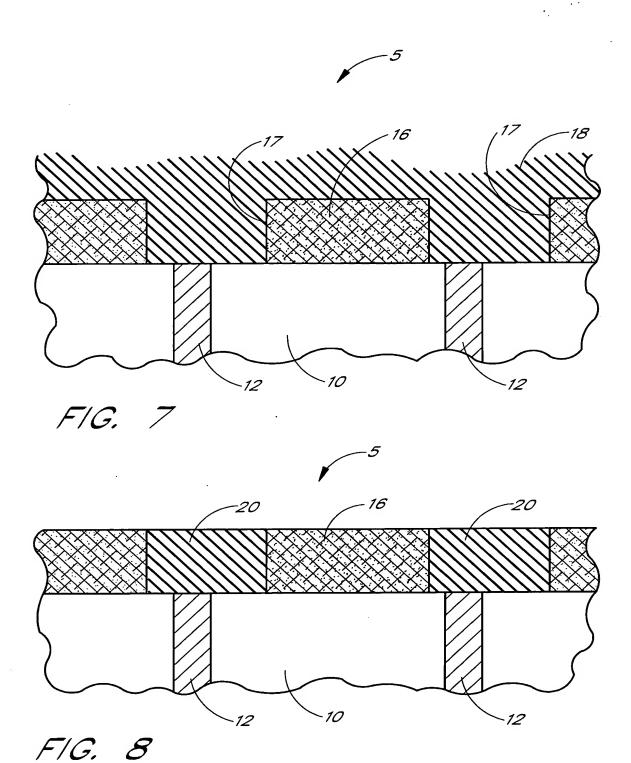
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F/G. 6

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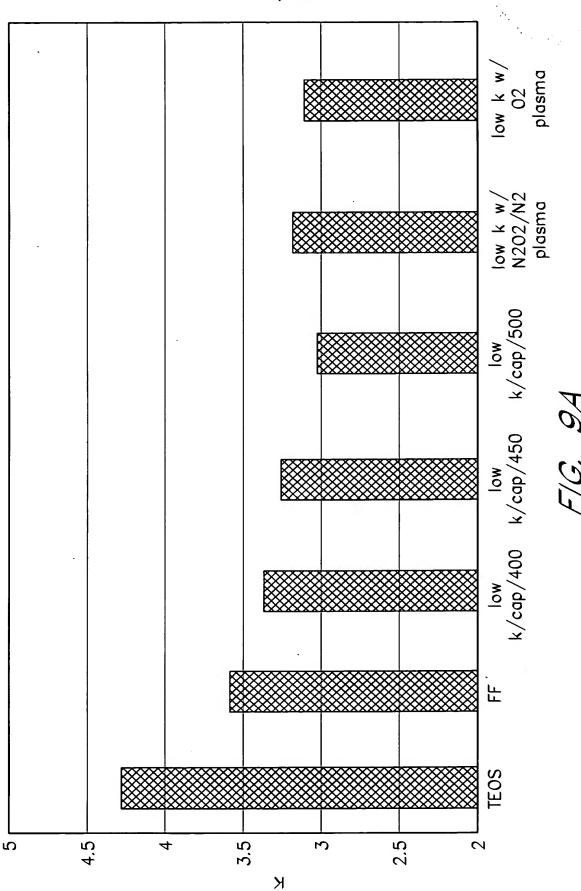


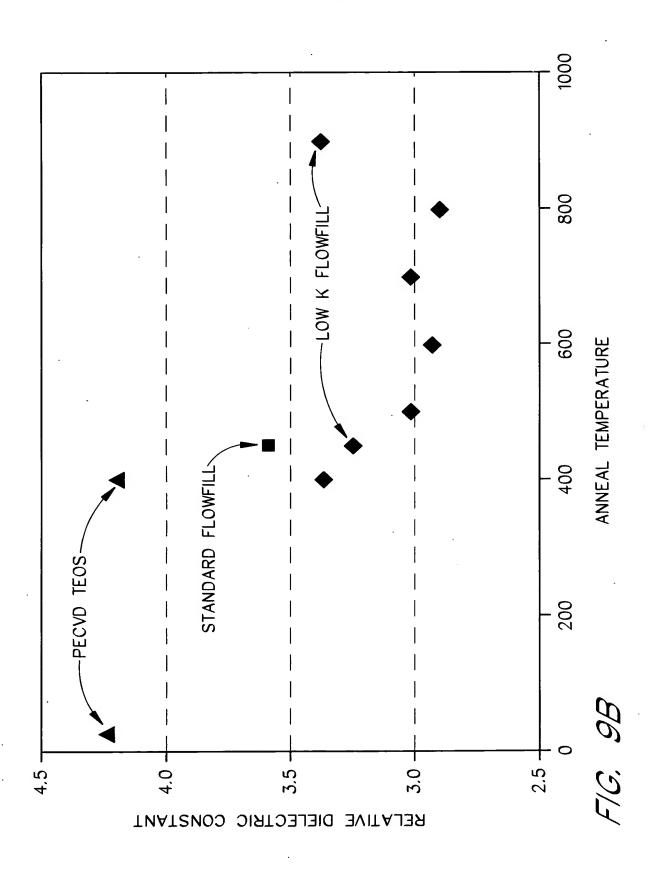
APPROVED O.G. FIG. LOW DIELECTRIC CONSTANT MATERIAL FOR INTEGRATE CIRCUIT FABRICATION

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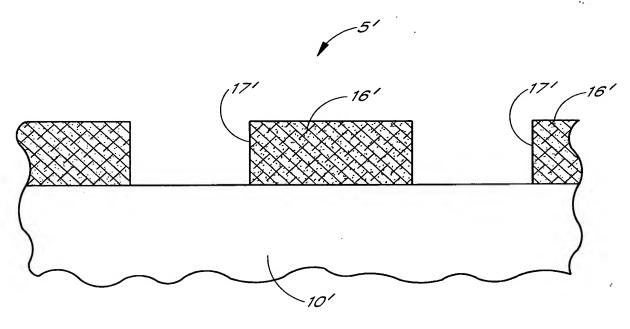
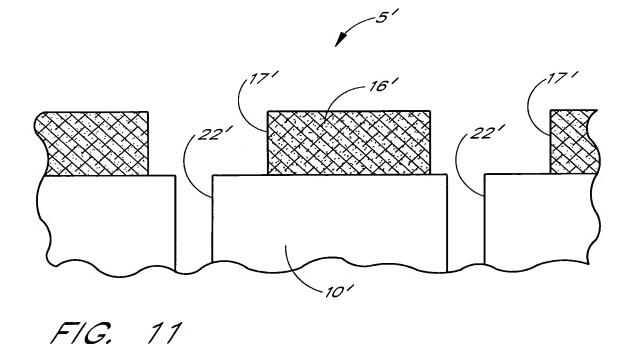


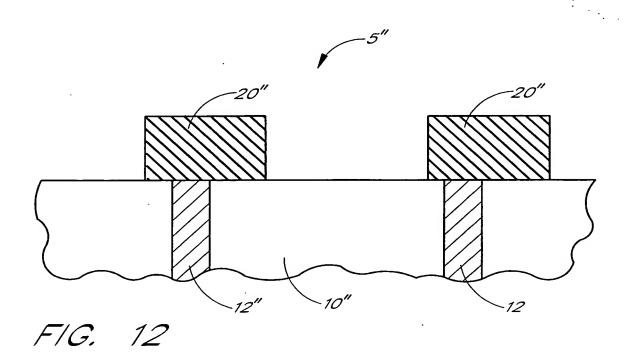
FIG. 10

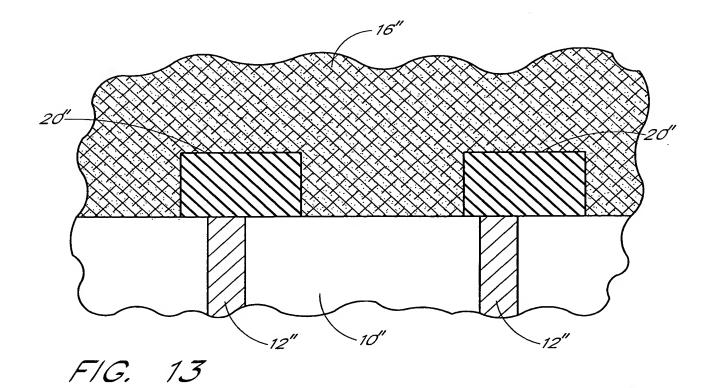


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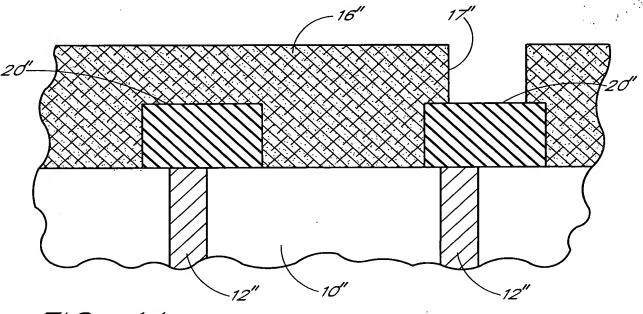
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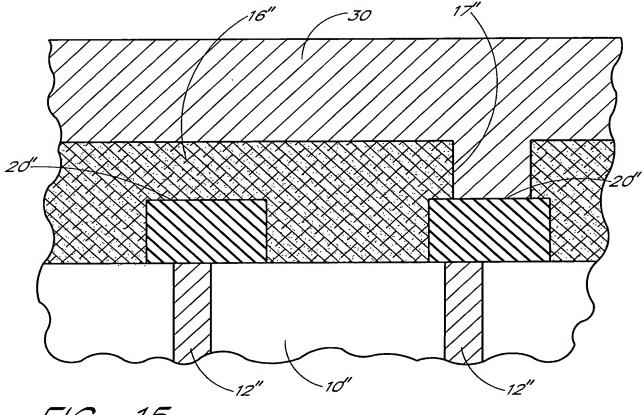








F/G. 14



F/G. 15

SURVESPIELECTRIC POSTANT MATERIAL FOR INTEGRATE
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CIRCUIT FABRICATION

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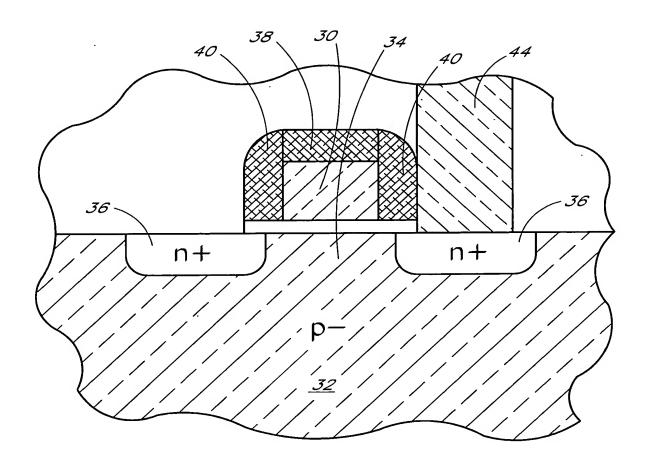


FIG. 16